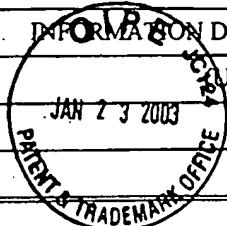


U.S. Department of Commerce, Patent and Trademark Office			Atty Docket No.		Application No.		
			NS-5127 US		10/054,653		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			Applicant(s)		Confirmation No.		
Substitute PTO Form 1449			Constantin Bulucea		9448		
			Filing Date		Group		
			January 18, 2002		2814		
U.S. Patent Documents							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA							
AB							
AC							
AD							
AE							
AF							
AG							
AH							
AI							
AJ							
AK							
Foreign Patent Documents							
						Translation	
	Document	Date	Country	Class	Subclass	Yes	No
AL							
AM							
AN							
AO							
AP							
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
DR	AQ	Takeuchi et al, "A New Multiple Transistor Design Methodology for High Speed Low Power SOCs," <u>IEDM Technical Digest</u> , December 2001, pages 22.6.1 - 22.6.7					
	AR						
	AS						
Examiner <u>DR</u>		Date Considered <u>9/3/05</u>					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.							

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O I P E (Use several sheets if necessary)				Constantin Bulucea		9448	
JAN 23 2003 P A T E N T & T R A D E M A R K O F F I C E				Filing Date		Group	
				January 18, 2002		2814	
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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	AB						
	AC						
	AD						
	AE						

## Foreign Patent Documents

		Document	Date	Country	Class	Subclass	Translation	Yes	No
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